Epitaxial growth of high mobility Bi$_2$Se$_3$ thin films on CdS

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We report the experiment of high quality epitaxial growth of Bi$_2$Se$_3$ thin films on hexagonal CdS (0001) substrates using a solid source molecular-beam epitaxy system. Layer-by-layer growth of single crystal Bi$_2$Se$_3$ has been observed from the first quintuple layer. The size of surface triangular terraces has exceeded 1 μm. Angle-resolved photoemission spectroscopy clearly reveals the presence of Dirac-cone-like dispersion surface states. Magneto-transport measurements demonstrate a high Hall mobility of $\sim$6000 cm$^2$/V s for the as-grown Bi$_2$Se$_3$ thin films at temperatures below 30 K. These characteristics of Bi$_2$Se$_3$ thin films promise a variety of potential applications in ultrafast, low-power dissipation devices. © 2011 American Institute of Physics. [doi:10.1063/1.3599540]

Topological insulators (TIs) have become the most intriguing materials in condensed matter physics and material science ever since the prediction of the existence of their non-trivial surface states.$^{1-3}$ In 2009, three-dimensional TIs were first proposed by Zhang et al. and have been globally focused thereafter.$^4$ Although semiconductor behaviors are maintained in the bulk, the surface states display a Dirac-cone-like dispersion relationship due to strong spin-orbit interaction, and the surface conductance should be protected by the time-reversal-symmetry (TRS).$^4-6$ The nature of this surface state provides a variety of fascinating physical phenomena, and the gapless surface also enables quasi-superconducting transport.$^7-14$ All of these unique properties make TIs one of the most promising candidates for nanoelectronics, spintronics, and quantum computing applications.$^{10, 12, 15}$

Recently, TI thin films grown by MBE have been reported on Si(111),$^{16-21}$ SiC (0001),$^{22}$ GaAs (111),$^{23}$ and other insulating substrates like α-Al$_2$O$_3$ (0001) and SrTiO$_3$ (111).$^{25}$ However, these substrates so far have relatively large lattice mismatch with the grown TI materials, resulting in a (quasi-) Van der Waals growth at the early stage of growth, so that the sizes of surface terraces were limited within 300 nm. Moreover, the film qualities were further restricted by the sacrificial layers at the interface, such as the Bi wetting layer or amorphous layers which are used to suppress the dangling bonds and decouple the thin films from their underlying substrates.$^{17, 21}$ Such drawbacks can greatly degrade the transport properties.

In this letter, we report the epitaxial growth of high-quality Bi$_2$Se$_3$ films on the lattice-matched insulating substrate material, i.e., hexagonal CdS (0001), using a solid source MBE system. We demonstrate the crystalline of Bi$_2$Se$_3$ starting from the first quintuple layer (QL). More importantly, we show a good surface quality of the grown Bi$_2$Se$_3$ thin film with the largest triangular terrace sizes grown by MBE that far. This surface improvement also produces a high Hall mobility at low temperatures, and makes the TI based high-speed devices possible.

Experimentally, our MBE growth was performed in an ultrahigh vacuum system. The epi-ready semi-insulating CdS (0001) substrates ($E_g$=2.42 eV) with a resistivity of $10^2$ Ω·cm were first degassed at 400 °C inside the MBE chamber for 2 h before sample growth. The epitaxial growth was conducted under a Se-rich environment, and detail growth information can be found elsewhere.$^{20}$ In-situ growth dynamics were monitored by real-time high-energy electron diffraction (RHEED) measurements. The sharp streaky patterns in Fig. 1(a) indicate the atomically flat surface morphology during the growth. The intensity of the specular spot was tracked, as shown in Fig. 1(b). The layer-by-layer RHEED oscillations were clearly observed right at the beginning of the growth, which provides strong evidence of epitaxial growth from the first layer. Meanwhile, by fitting the oscillation curve with a damped sinusoidal function, the growth rate can be estimated as 0.55 QL/min.

Atomic force microscope (AFM) was performed to investigate the surface morphology of the Bi$_2$Se$_3$ thin film. Figure 1(c) shows a typical AFM image of an as-grown Bi$_2$Se$_3$ film with a thickness of 49 QLs. Characteristically, triangle-shaped terraces were observed. Compared with reported data, the terrace size of our Bi$_2$Se$_3$ thin films was significantly increased to $\sim$1 μm, and the root mean square (RMS) surface roughness was well controlled to below 0.5 nm. This extraordinary improvement of the surface quality comes from the advantage of the epitaxial growth of the lattice-matched Bi$_2$Se$_3$–CdS system (note $a_{\text{Bi}_2\text{Se}_3}$ =4.13 ± 0.1 Å and $a_{\text{CdS}}$=4.138 Å$^{18, 26}$ which inherently promotes a smooth two-dimensional (2D) growth without having sacrificial amorphous layers at the initial growth. Furthermore, Fig. 1(d) shows the height profile of the red solid line marked in Fig. 1(c). The height of each step is $\sim$0.95 nm, which is consistent with the reported thickness of one individual Bi$_2$Se$_3$ QL.$^{27}$ In order to understand the

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interface between the substrate and the Bi$_2$Se$_3$ thin film, high-resolution transmission electron microscopy (HRTEM) was performed and the result is shown in Fig. 1(e), in which atomically flat interface is clearly observed, as marked by a dashed line. This result is consistent with our real-time RHEED observation outlined above. The layered structures of the single crystal Bi$_2$Se$_3$ are clearly seen in Fig. 1(e) and no amorphous layer or other sacrificial layer in the interface can be observed. The lattice spacing between (0003) planes is measured to be ~1 nm, as indicated by two paralleled white lines in Fig. 1(e), which agrees with other reports.\textsuperscript{17,20}

The electronic structure of the Bi$_2$Se$_3$ thin film grown on CdS substrate was studied by angle-resolved photoemission spectroscopy (ARPES). Samples with atomically clean surfaces suitable for ARPES were prepared by mild annealing at $T=200$ °C in the experimental chamber for two hours. All faces suitable for ARPES were prepared by mild annealing at temperature fell below 30 K. This Hall mobility exceeds previously reported data,\textsuperscript{17,22} and is also comparable with those obtained by other chemical methods.\textsuperscript{29,30} Such enhanced mobility is attributed from the good surface quality. When the majority of the bulk carriers are frozen out at very low temperature, the surface conductance component begins to become more prominent. For an ideal flat 2D surface, back-scattering should be prevented owing to the TRS held by TI materials.\textsuperscript{10} However, isolated terraces were inevitably formed on the surface during growth. This surface roughness would possibly result in inter-terrace scattering, and thus degrades the mobility. Alternatively, this degradation can be effectively inhibited once the terrace density is reduced. This explains the case of our thin film growth on the CdS substrate as evidenced in Fig. 1. It should be noted that the mobility we obtained is the effective value because the overall conductance is the superposition of both the surface and

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**FIG. 1.** (Color online) (a) RHEED pattern along [1120] direction of an as-grown surface of Bi$_2$Se$_3$ with a thickness of 49 QLs. (b) RHEED oscillations of intensity measured (blue, solid) and fitted curve (red, dashed) of the specular beam. The oscillation period is found to be 110 s, corresponding to a growth rate of ~0.55 QL/min. (c) AFM image of the Bi$_2$Se$_3$ thin film with the size of 1 μm×1 μm. (d) The height profile along the solid red line marked in (c), showing a step size of 0.95 nm. (e) HRTEM of a Bi$_2$Se$_3$ grown on a CdS (0001) substrate.

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**FIG. 2.** (Color online) (a) Core level photoemission of the Bi$_2$Se$_3$ thin film grown on the CdS substrate with the thickness of 49 QL. Both Se and Bi core levels are measured with 100 eV photons. Inset: LEED pattern of the Bi$_2$Se$_3$ thin film showing a (1 × 1) plane structure. (b) ARPES intensity map of the 49 QL Bi$_2$Se$_3$ thin film along Γ–K direction. The data were taken using 52 eV photons.
the bulk. Therefore, to extract the accurate value of surface mobility, thickness dependence measurements should be added in future experiments.

In conclusion, we have demonstrated high quality epitaxial growth of Bi$_2$Se$_3$ thin films on lattice matched CdS substrate using MBE. The AFM results reveal a good surface morphology and the largest triangular terrace size around 1 µm. HRTEM experiments show no amorphous layer at the interface, on the contrast of the interface on Si (111), indicating that the layer-by-layer growth mode is achieved from the very beginning. The ARPES data demonstrate the single Dirac-cone-like nontrivial surface state with the Fermi level located within the bulk band gap. More importantly, the Hall bar device fabricated on our Bi$_2$Se$_3$ thin films exhibits a high Hall mobility of more than 6000 cm$^2$/Vs under low temperature. This can be attributed to the suppression of interterrace scattering with improved thin film quality. It is important to further increase the terrace and step sizes so that better transport properties can be achieved on the lattice-matched CdS substrate. This thin film quality improvement will provides an important step toward the realization of innovations for future nanoelectronics and spintronics devices.

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